TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE (L^2-π-MOSV)

2SJ464

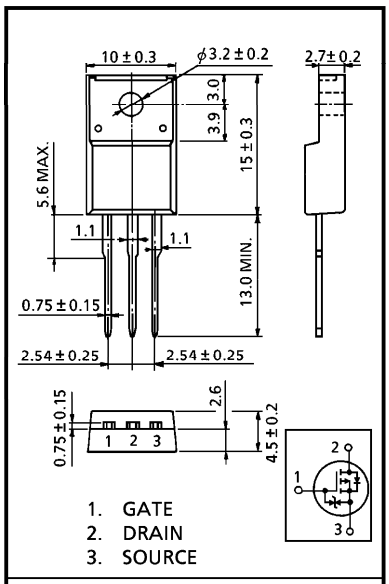
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS

- 4V Gate Drive
- Low Drain-Sorce ON Resistance : $R_{DS\,(ON)}=64m\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}|=15S$ (Typ.)
- Low Leakage Current : $I_{DSS}=-100\mu A$ (Max.) ($V_{DS}=-100V$)
- Enhancement-Mode : $V_{th}=-0.8\sim-2.0V$ ($V_{DS}=-10V$, $I_D=-1mA$)

Unit in mm



JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1B

Weight : 1.9g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	−100	V
Drain-Gate Voltage ($R_{GS}=20k\Omega$)		V_{DGR}	−100	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	DC	I_D	−18	A
	Pulse	I_{DP}	−72	
Drain Power Dissipation (Tc=25°C)		P_D	45	W
Single Pulse Avalanche Energy**		E_{AS}	937	mJ
Avalanche Current		I_{AR}	−18	A
Repetitive Avalanche Energy*		E_{AR}	4.5	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th\,(ch-c)}$	2.78	°C / W
Thermal Resistance, Channel to Ambient	$R_{th\,(ch-a)}$	62.5	°C / W

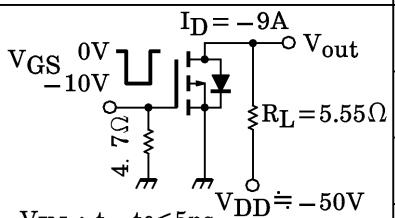
Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD}=-50V$, Starting $T_{ch}=25°C$, $L=3.56mH$, $R_G=25\Omega$, $I_{AR}=-18A$

This transistor is an electrostatic sensitive device.
Please handle with caution.

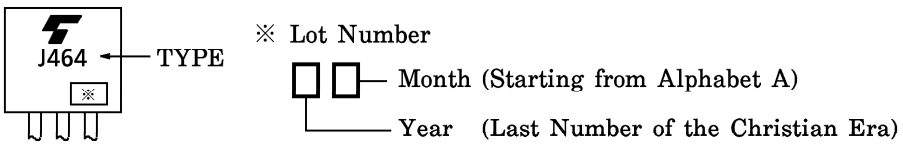
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

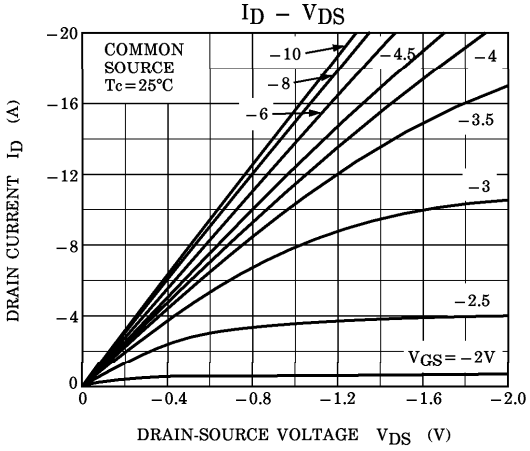
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V$, $V_{DS} = 0V$	—	—	±10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = -100V$, $V_{GS} = 0V$	—	—	−100	μA
Drain-Source Breakdown Voltage		$V_{(BR)\,DSS}$	$I_D = -10mA$, $V_{GS} = 0V$	−100	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = -10V$, $I_D = -1mA$	−0.8	—	−2.0	V
Drain-Source ON Resistance		$R_{DS\,(ON)}$	$V_{GS} = -10V$, $I_D = -9A$	—	64	90	mΩ
			$V_{GS} = -4V$, $I_D = -9A$	—	85	120	
Forward Transfer Admittance		$\|Y_{fs}\|$	$V_{DS} = -10V$, $I_D = -9A$	7	15	—	S
Input Capacitance		C_{iss}	$V_{DS} = -10V$, $V_{GS} = 0V$, f = 1MHz	—	2900	—	pF
Reverse Transfer Capacitance		C_{rss}		—	480	—	
Output Capacitance		C_{oss}		—	1000	—	
Switching Time	Rise Time	t_r	 V_{IN} : t_r, $t_f < 5ns$, Duty ≦ 1%, $t_w = 10\mu s$	—	25	—	ns
	Turn-on Time	t_{on}		—	45	—	
	Fall Time	t_f		—	25	—	
	Turn-off Time	t_{off}		—	170	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \fallingdotseq -80V$, $V_{GS} = -10V$, $I_D = -18A$	—	140	—	nC
Gate-Source Charge		Q_{gs}		—	90	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	50	—	

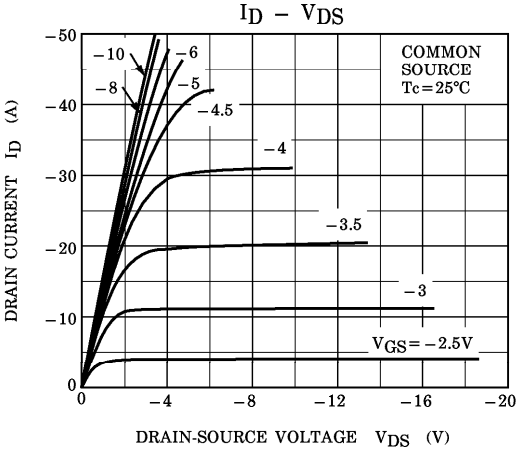
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

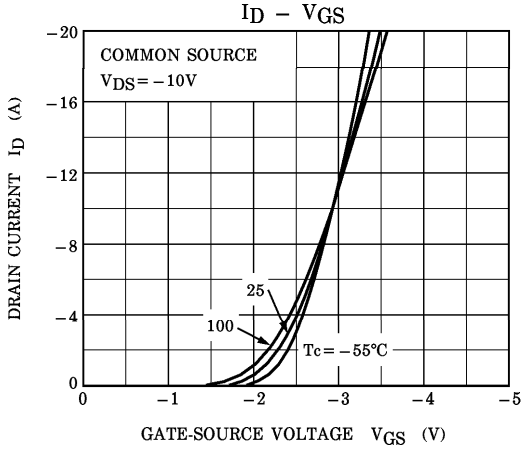
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	−18	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	−72	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = -18A$, $V_{GS} = 0V$	—	—	1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = -18A$, $V_{GS} = 0V$	—	220	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 50A/\mu s$	—	0.97	—	μC

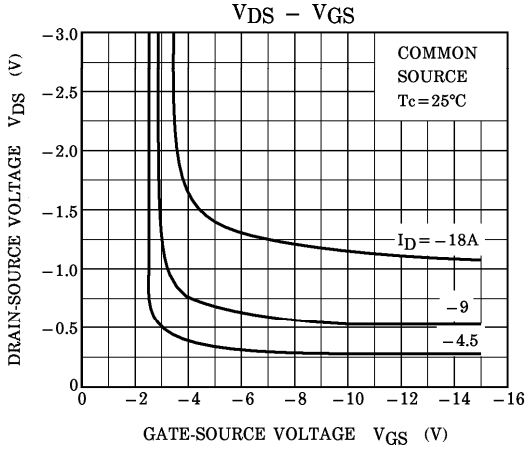
MARKING

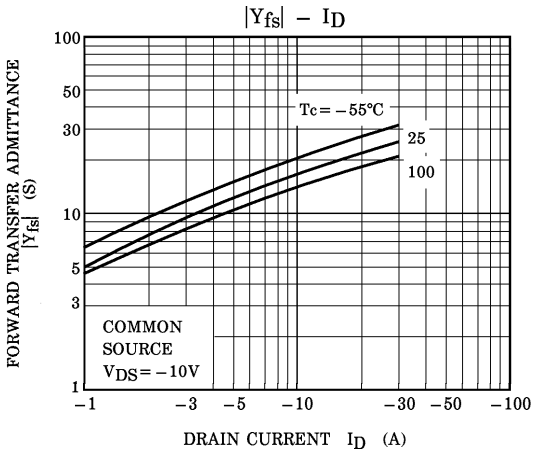


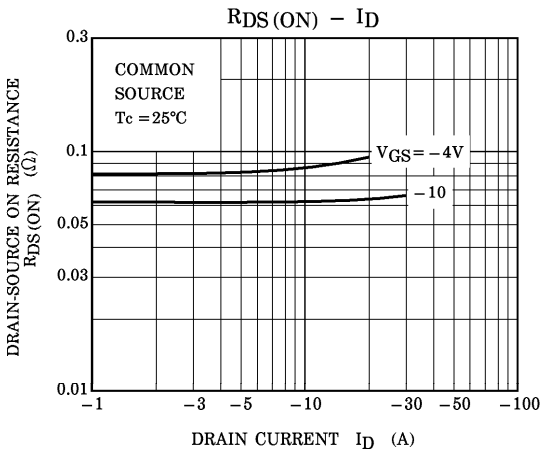




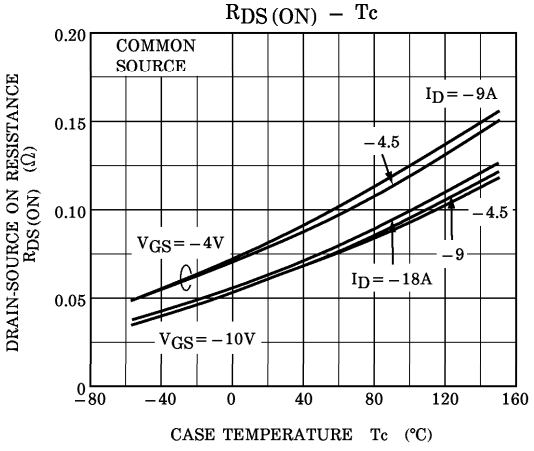




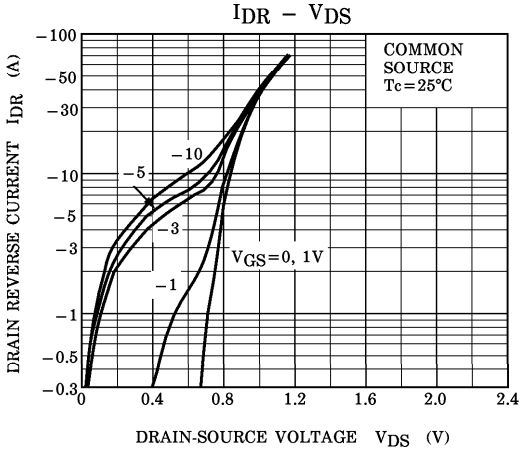




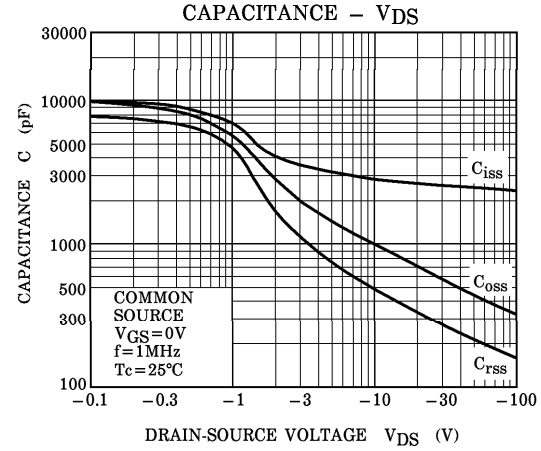
$R_{DS(ON)}$ – Tc



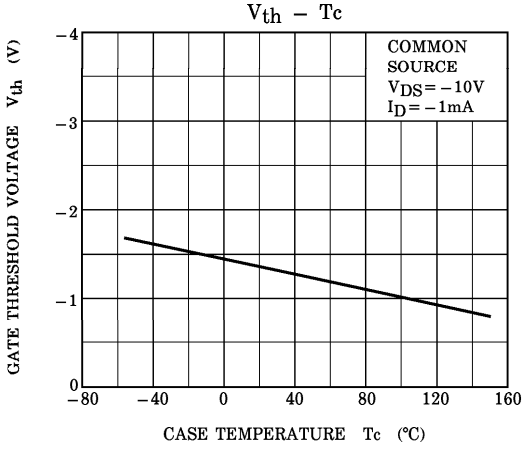
I_{DR} – V_{DS}



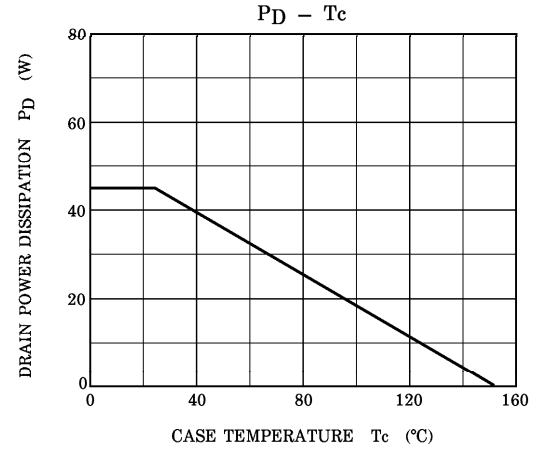
CAPACITANCE – V_{DS}



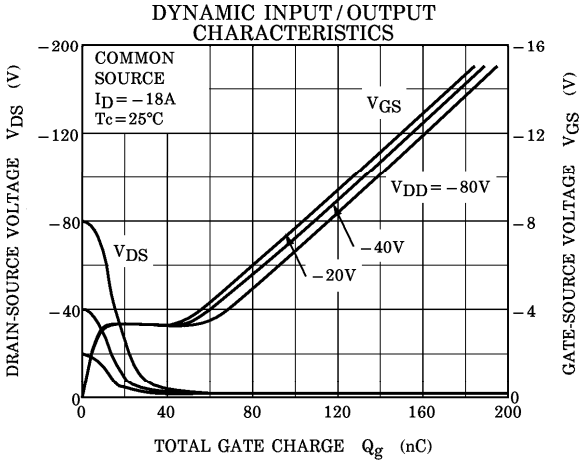
V_{th} – Tc



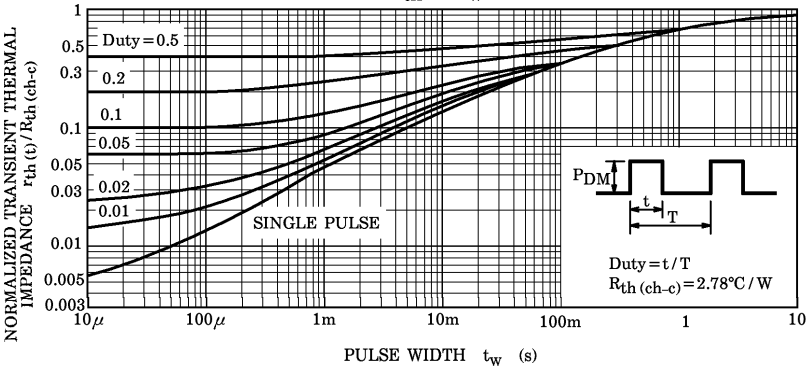
P_D – Tc



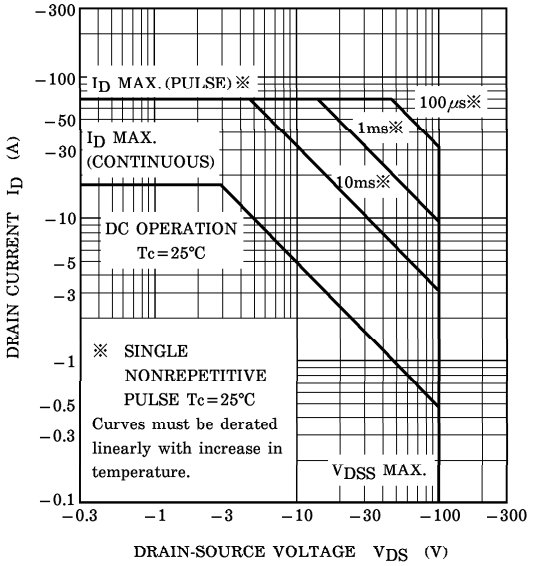
DYNAMIC INPUT / OUTPUT CHARACTERISTICS



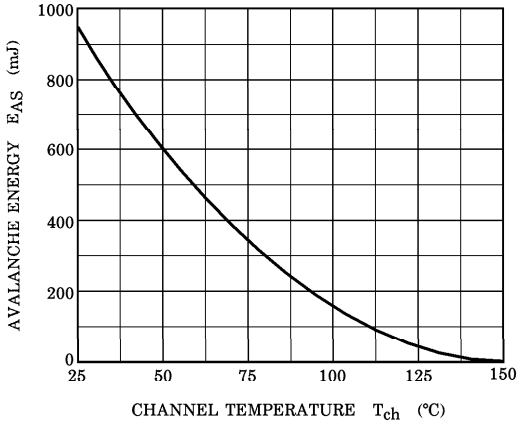
$r_{th} - t_w$

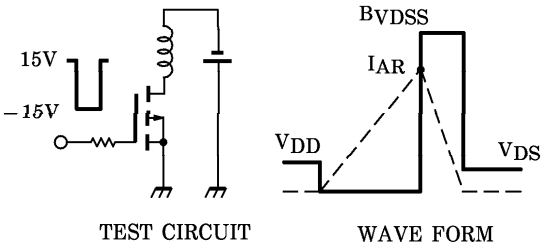


SAFE OPERATING AREA



$E_{AS} - T_{ch}$





Peak $I_{AR} = -18A$, $R_G = 25\Omega$
$V_{DD} = -50V$, L = 3.56mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$